

Low voltage dual brush DC motor driver

CITY CHILLIS

VFQFPN 3 X 3 X 1.0 (16-pin)

Features

- Operating voltage from 1.8 to 10 V
- Maximum output current 1.3 Arms
- $R_{DS(ON)}$ HS + LS = 0.4 Ω typ.
- · Current control with adjustable off-time
- Full protection set
 - Non-dissipative overcurrent protection
 - Short-circuit protection
 - Thermal shutdown
- Energy saving and long battery life with standby consumption less than 80 nA



Application

- Battery-powered DC motor applications such as:
 - Tovs
 - Portable printers
 - Robotics
 - Point of sale (POS) devices
 - Portable medical equipment
 - Healthcare and wellness devices (shavers and toothbrushes)

Product status link

STSPIN240

Product label



Description

The STSPIN240 is a dual brush DC motor driver integrating a low $R_{DS(ON)}$ power stage in a small QFN 3 x 3 mm package.

Both the full-bridges implement an independent PWM current controller with fixed OFF time

The device is designed to operate in battery-powered scenarios and can be forced in a zero-consumption state, allowing a significant increase in battery life.

The STSPIN240 offers a complete set of protection including overcurrent, overtemperature and short-circuit protection.

OUTB1

OUTB2

SENSEB

Brush DC



Block diagram

STBY\RESET

REF EN\FAULT

PHA

PWMA

PHB

PWMB

TOFF

Oscilator

VS OUTA1 Brush DC OUTA2 SENSEA Control Logic

Figure 1. Block diagram

OVT

GND

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2 Electrical data

2.1 Absolute maximum ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Test Condition	Value	Unit
Vs	Supply voltage		-0.3 to 11	V
V _{IN}	Logic input voltage		-0.3 to 5.5	V
V _{OUT} – V _{SENSE}	Output to sense voltage drop		up to 12	V
V _S – V _{OUT}	Supply to output voltage drop		up to 12	V
V _{SENSE}	Sense pins voltage	Sense pins voltage		V
I _{OUT,RMS}	Continuous power stage output current (each bridge)		1.3	A _{rms}
T _{j,OP}	Operative junction temperature		-40 to 150	°C
T _{j,STG}	Storage junction temperature		-55 to 150	°C

2.2 Recommended operating conditions

Table 2. Recommended operating conditions

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
Vs	Supply voltage		1.8	-	10	V
V _{IN}	Logic input voltage		0	-	5	V
V _{REF}	Reference voltage input		0.1	-	0.5	V

2.3 Thermal data

Table 3. Thermal data

Symbol	Parameter	Conditions		Unit
R _{thJA}	Junction-to-ambient thermal resistance	Natural convection, according to JESD51-2A ⁽¹⁾	57.1	°C/W
R _{thJCtop}	Junction-to-case thermal resistance (top side)	Simulation with cold plate on package top	67.3	°C/W
R _{thJCbot}	Junction-to-case thermal resistance (bottom side)	Simulation with cold plate on exposed pad	9.1	°C/W
R _{thJB}	Junction-to-board thermal resistance	according to JESD51-8 (1)	23.3	°C/W
ΨЈТ	Junction-to-top characterization	According to JESD51-2A (1)	3.3	°C/W
ΨЈВ	Junction-to-board characterization	According to JESD51-2A (1)	22.6	°C/W

^{1.} Simulated on a 21.2x21.2 mm board, 2s2p 1 Oz copper and four 300 μm vias below exposed pad

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2.4 ESD protection ratings

Table 4. ESD protection ratings

Symbol	Parameter	Conditions	Class	Value	Unit
НВМ	Human body model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	H2	2	kV
CDM	Charge device model	Conforming to ANSI/ESDA/JEDEC JS-001-2014	C2a	500	V

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3 Electrical characteristics

Table 5. Electrical characteristics

Testing conditions: V_S = 5 V, T_j = 25 °C unless otherwise specified.

Symbol	Parameter	Test condition	Min	Тур	Max	Unit	
Supply							
V _{Sth(ON)}	V _S turn-on voltage	V _S rising from 0 V	1.45	1.65	1.79	V	
V _{Sth(OFF)}	V _S turn-off voltage	V _S falling from 5 V	1.3	1.45	1.65	V	
V _{Sth(HYS)}	V _S hysteresis voltage			180		mV	
1	V complex company	No commutations, EN\FAULT = 0 R_{OFF} = 160 k Ω		960	1300	μΑ	
Is	V _S supply current	No commutations, EN\FAULT = 1 R _{OFF} = 160 k Ω		1500	1950	μΑ	
I _{S,STBY}	V _S standby current	STBY = 0 V		10	80	nA	
V _{STBYL}	Standby low voltage				0.9	V	
V _{STBYH}	Standby high voltage		1.48			V	
Power stage							
		V _S = 10 V, I _{OUT} = 1.3 A		0.4	0.65		
R _{DS(ON)HS+LS}	Total on resistance HS + LS	$V_S = 10 \text{ V}, I_{OUT} = 1.3 \text{ A}$ $T_j = 125 ^{\circ}\text{C}^{-(1)}$		0.53	0.87	Ω	
		V _S = 3 V, I _{OUT} = 0.4 A		0.53	0.8		
I _{DSS} Le	Leakage current	OUTx = V _S			1	μA	
		OUTx = GND	- 1				
V _{DF}	Freewheeling diode forward voltage	I _D = 1.3 A		0.9		V	
t _{rise}	Rise time	V _S = 10 V; unloaded outputs		10		ns	
t _{fall}	Fall time	V _S = 10 V; unloaded outputs		10		ns	
t _{DT}	Integrated dead time			50		ns	
PWM current	controller						
V _{SNS,OFFSET}	Sensing offset	V _{REF} = 0.1 V	-15		+15	mV	
		$R_{OFF} = 10 \text{ k}\Omega$		9		μs	
t _{OFF}	Total OFF time	R _{OFF} = 160 kΩ		125		μs	
Δf _{OSC}	Internal oscillator precision (fosc/fosc, ID)	R _{OFF} = 20 kΩ	-20%		+20%	-	
t _{OFF,jitter}	Total OFF time jitter	R _{OFF} = 10 kΩ		2%		-	
Logic IOs	<u> </u>	I					
V _{IH}	High logic level input voltage		1.6			V	
V _{IL}	Low logic level input voltage				0.6	V	
V _{RELEASE}	EN\FAULT open drain release voltage				0.4	V	
V _{OL}	EN\FAULT Low logic level output voltage	I _{EN} = 4 mA			0.4	V	
R _{STBY}	STBY pull-down resistance			36		kΩ	

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Symbol	Parameter	Test condition	Min	Тур	Max	Unit
I _{PDEN}	EN\FAULT pull-down current			10.5		μΑ
t _{ENd}	EN\FAULT input propagation delay	From EN\FAULT falling edge to OUT high impedance		55		ns
t _{PWM,d(ON)}	PWMx turn-on propagation delay	Refer to Figure 4		125		ns
t _{PWM,d(OFF)}	PWMx turn-off propagation delay	Refer to Figure 4		140		ns
t _{PH,d}	PHx propagation delay	Refer to Figure 4		125		ns
Protections						
T _{jSD}	Thermal shutdown threshold			160		°C
T _{jSD,Hyst}	Thermal shutdown hysteresis			40		°C
loc	Over-current threshold	See Figure 14		2		Α

^{1.} Based on characterization data on a limited number of samples, not tested during production.

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4 Pin description

STBY\ RESET PWMB PHB EN\FAULT 13 16 15 (12 PHA TOFF (11 **PWMA** REF EPAD (10 OUTA1 OUTB1 (9 4) SENSEA SENSEB ¦ 8 ¦ OUTA2 VS GND OUTB2

Figure 2. Pin connection (top view)

Note: The exposed pad must be connected to ground.

Table 6. Pin description

No.	Name	Туре	Function
1	PHA	Logic input	Phase input for bridge A
2	PWMA	Logic input	PWM input for bridge A
3	OUTA1	Power output	Power bridge output side A1
4	SENSEA	Power output	Sense output of the bridge A
5	OUTA2	Power output	Power bridge output side A2
6	VS	Supply	Device supply voltage
7, EPAD	GND	Ground	Device ground
8	OUTB2	Power output	Power bridge output side B2
9	SENSEB	Power output	Sense output of the bridge B
10	OUTB1	Power output	Power bridge output side B1
11	REF	Analog input	Reference voltage for the current limiter circuitry
12	TOFF	Analog input	Internal oscillator frequency adjustment
			Logic input 5 V compliant and open drain output.
13	EN\FAULT	Logic input\ Open drain output	This is the enable of the power stage (when low the power stage is turned off) and it is forced low by the integrated open-drain MOSFET when a failure occurs.
14	STBY\RESET	Logic input	Logic input 5 V compliant.
	OTDT WESET	Logic input	When forced low the device is forced in low consumption mode.
15	PHB	Logic input	Phase input for bridge B
16	PWMB	Logic input	PWM input for bridge B

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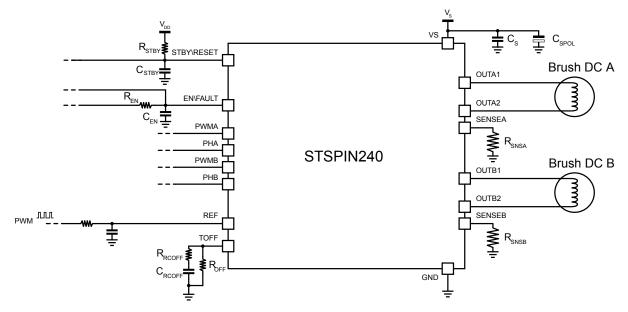


5 Typical applications

Table 7. Typical application value

Name	Value
Cs	2.2 μF / 16 V
C _{SPOL}	22 μF / 16 V
R _{SNSA} , R _{SNSB}	330 mΩ / 1 W
C _{EN}	10 nF / 6.3 V
R _{EN}	18 kΩ
C _{STBY}	1 nF / 6.3 V
R _{STBY}	18 kΩ
C _{RCOFF}	22 nF
R _{RCOFF}	1 kΩ
R _{OFF}	47 kΩ ($t_{OFF} \cong 37 \ \mu s$)

Figure 3. Typical application schematic



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6 Description

The STSPIN240 is a dual brush DC motor driver integrating two PWM current controllers and a power stage composed by two fully-protected full-bridges.

6.1 Standby and power-up

The device provides a low consumption mode, which is set forcing the STBY\RESET input below the V_{STBYL} threshold.

When the device is in the standby status, the power stage is disabled (outputs are in high impedance) and the supply to the integrated control circuitry is cut off. When the device leaves the standby status, all the control circuitry is reset at power-up condition.

At power-up, power-down and when leaving the standby condition, the EN\FAULT pin is forced low until the internal circuitry stabilize.

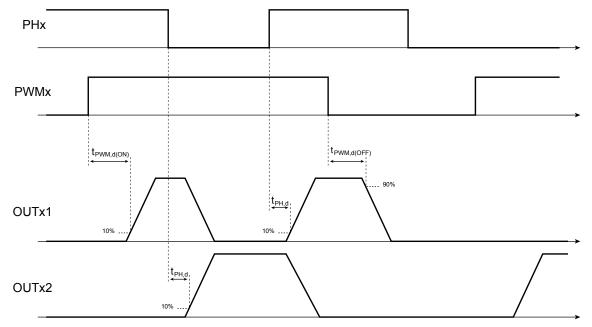
6.2 Motor driving

The outputs of each half-bridge is controlled by the respective PWMx and PHx inputs as listed in Table 8.

EN\FAULT Full-bridge condition PHx **PWMx** OUT_{x2} OUTx1 0 Χ Χ HiZ HiZDisabled 1 0 0 **GND GND** Both LS on 1 0 1 **GND** VS HS2 and LS1 on (current X1 ← X2) **GND GND** Both LS on 1 1 0 1 1 VS **GND** HS1 and LS2 on (current $X1 \rightarrow X2$) 1

Table 8. STSPIN240 truth table





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6.3 PWM current control

The device implements two independent PWM current controllers, one for each full bridge.

The voltage of the sense pins (V_{SENSEA} and V_{SENSEB}) is compared to the reference voltage applied on the REF pin (V_{REF}).

When $V_{SENSEX} > V_{REF}$, the current limiter is triggered, the OFF time counter is started and the decay sequence is performed.

The decay sequence turns on both the low sides of the full bridge for the entire duration of the OFF time.

Table 9. ON and slow decay states

PHx	PWMx	ON	Decay ⁽¹⁾
		HSx1 = OFF	
0	0	LSx1 = ON	N.A.
0		HSx2 = OFF	N.A.
		LSx2 = ON	
	1	HSx1 = OFF	HSx1 = OFF
0		LSx1 = ON	LSx1 = ON
0		HSx2 = ON	HSx2 = OFF
		LSx2 = OFF	LSx2 = ON
		HSx1 = OFF	
1	0	LSx1 = ON	NI A
'	0	HSx2 = OFF	N.A.
		LSx2 = ON	
	HSx1 = ON LSx1 = OFF	HSx1 = ON	HSx1 = OFF
4		LSx1 = OFF	LSx1 = ON
1	1	HSx2 = OFF	HSx2 = OFF
		LSx2 = ON	LSx2 = ON

^{1.} During decays the inputs values are ignored until the system returns to ON condition (decay time expired).

The reference voltage value, V_{REF}, must be selected according to the load current target value (peak value) and sense resistor value.

Equation 1

(1)

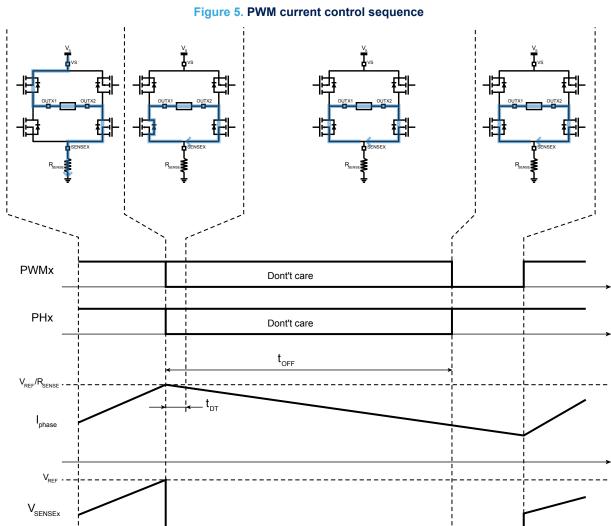
 $V_{REF} = R_{SNSx} \cdot I_{LOAD,peak}$

When choosing the sense resistor value, two main issues must be taken into account:

- The sense resistor dissipates energy; for this reason the resistance of this component should be kept low.
- The lower the R_{SNSx} value, the higher the peak current error due to noise on the V_{REF} pin and the input offset of the current sense comparator. Values of R_{SNSx} that are too low must be avoided.

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6.3.1 OFF time adjustment

The total OFF time is adjusted through an external resistor connected between the TOFF pin and ground, as shown in Figure 6. A small RC series must be inserted in parallel with the regulator resistor in order to increase the stability of the regulation circuit according to indications listed in Table 10.

R_{RCOFF} R_{OFF}

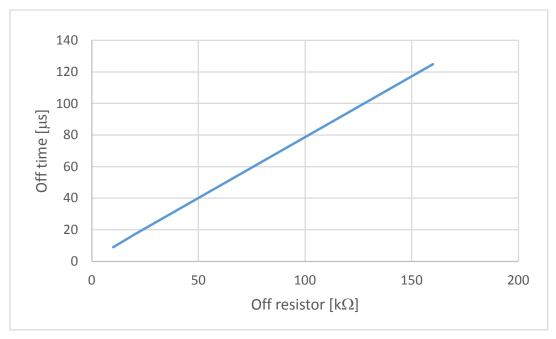
Figure 6. OFF time regulation circuit

The relationship between the OFF time and the external resistor value is shown in Figure 7. The value typically ranges from 10 μ s to 150 μ s.

Table 10. Recommended R $_{\rm RCOFF}$ and C $_{\rm RCOFF}$ values according to R $_{\rm OFF}$

R _{OFF}	R _{RCOFF}	C _{RCOFF}
10 kΩ ≤ R _{OFF} < 82 kΩ	1 kΩ	22 nF
82 kΩ ≤ R_{OFF} ≤ 160 kΩ	2.2 kΩ	22 nF

Figure 7. OFF time vs. R_{OFF} value



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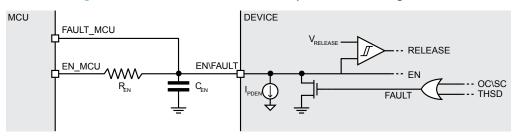
6.4 Overcurrent and short circuit protections

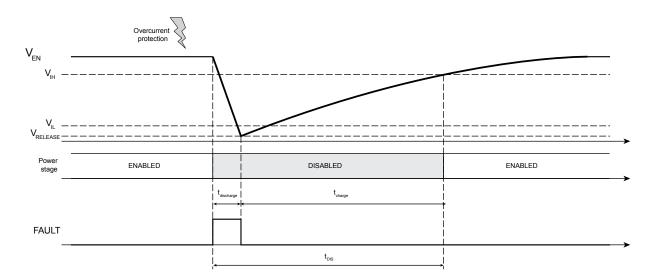
The device embeds a circuitry protecting each power output against the over load and short circuit conditions (short to ground, short to V_S and short between outputs).

When the overcurrent or the short circuit protection is triggered, the power stage is disabled and the EN\FAULT input is forced low by the integrated open-drain MOSFET discharging the external C_{EN} capacitor.

The power stage is kept disabled and the open-drain MOSFET is kept ON until the EN\FAULT input falls below the $V_{RELEASE}$ threshold, then the C_{EN} capacitor is charged through the R_{EN} resistor.

Figure 8. Overcurrent and short-circuit protections management





The total disable time after an overcurrent event can be set sizing properly the external network connected to the EN\FAULT pin (refer to Figure 9 and Figure 10).

Equation 2

(2)

$$t_{DIS} = t_{discharge} + t_{charge}$$

But t_{charge} is normally much higher than $t_{discharge}$ we can consider only the second contribution:

Equation 3

(3)

$$t_{DIS} \cong R_{EN} \cdot C_{EN} \cdot \ln \frac{(v_{\text{DD}} - R_{\text{EN}} \cdot I_{\text{PD}}) - v_{\text{RELEASE}}}{(v_{\text{DD}} - R_{\text{EN}} \cdot I_{\text{PD}}) - v_{\text{IH}}}$$

Where V_{DD} is the pull-up voltage of R_{EN} resistor.

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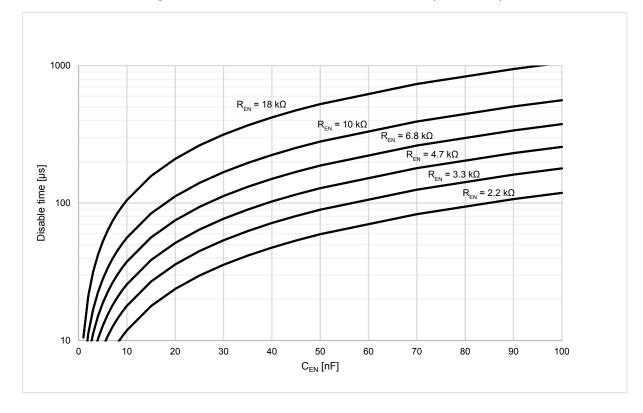
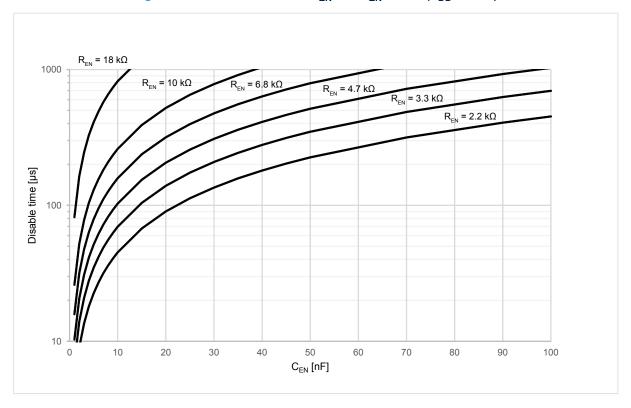


Figure 9. Disable time versus R_{EN} and C_{EN} values (V_{DD} = 3.3 V)





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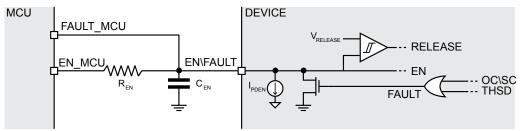
6.5 Thermal shutdown

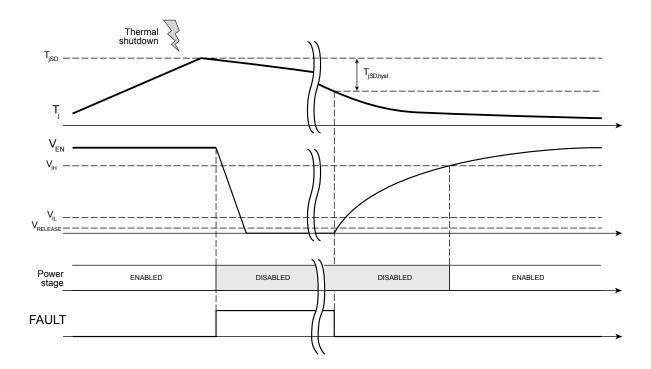
The device embeds a circuitry protecting it from the over-temperature conditions.

When the thermal shutdown temperature is reached the power stage is disabled and the EN\FAULT input is forced low by the integrated open-drain MOSFET (refer to Figure 11).

The protection and the EN\FAULT output are released when the IC temperature returns below a safe operating value $(T_{jSD} - T_{jSD,Hyst})$.

Figure 11. Thermal shutdown management





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7 Graphs

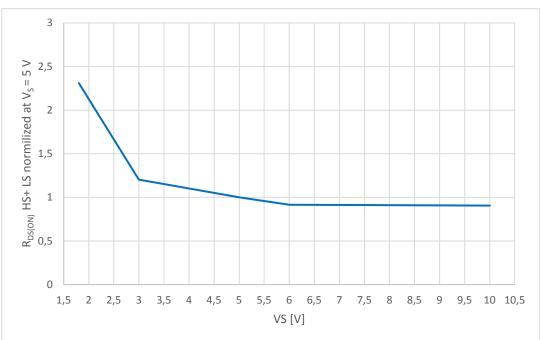
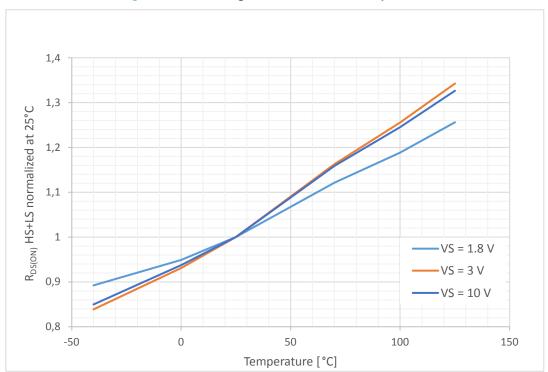


Figure 12. Power stage resistance versus supply voltage





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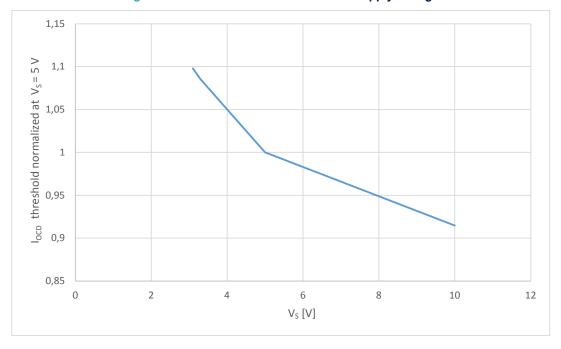


Figure 14. Overcurrent threshold versus supply voltage

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8 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

8.1 VFQFPN 3x3x1.0 16L package information

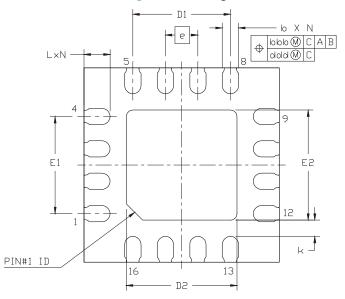
Table 11. Package dimensions

Cumbal		Dimensions [mm]				
Symbol	Min.	Тур.	Max.			
Α	0.80	0.90	1.00			
A1	0.00	0.02	0.05			
A3		0.20				
b	0.20	0.25	0.30			
D		3.00 BSC				
D1		1.50 BSC				
D2	1.60	1.70	1.80			
е		0.50 BSC				
E	3.00 BSC					
D2		1.50 BSC				
E2	1.60	1.70	1.80			
L	0.30	0.40	0.50			
k	0.20					
N		16				
aaa		0.15				
bbb		0.10				
ccc		0.10				
ddd		0.05				
eee		0.08				
fff		0.10				

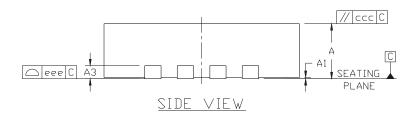
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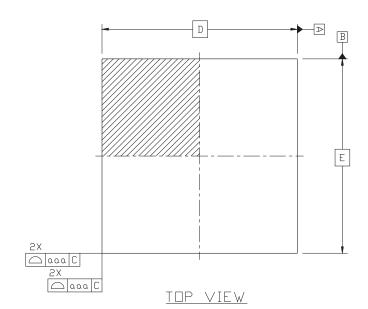


Figure 15. Package outline



BOTTOM VIEW





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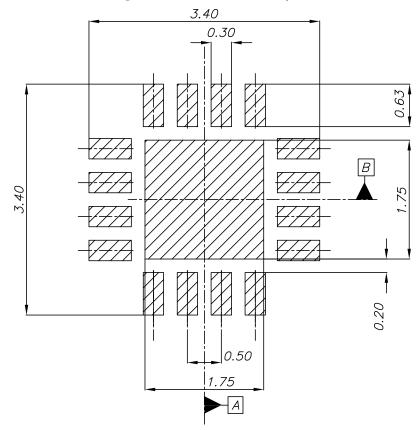


Figure 16. Recommended footprint

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Revision history

Table 12. Document revision history

Date	Version	Changes
06-May-2016	1	Initial release.
		Updated document status to Datasheet - production data on cover page.
30-Jun-2016	2	Updated Table 1 (changed Max. value of VS from 12 to 11).
		Updated Table 7 (changed value of t _{OFF} from 47 μs to 37 μs).
		Updated Figure 1 and Figure 12.
04-Nov-2016	-Nov-2016 3	Updated Table 2 (added t _{INw} parameter) and Table 3.
		Minor modifications throughout document.
		Updated Table 2 (removed t _{INw} parameter).
11-Aug-2017	4	Updated title of Figure 12 and Figure 13.
		Minor modifications throughout document.
		Updated Table 5 (modified test condition of V _{SNS,OFFSET} parameter).
13-Sep-2023	5	Updated Section 6.1 Standby and power-up.
13-36ρ-2023	3	Updated Figure 5, Figure 8 and Figure 11.
		Updated all data in Section 8.1 VFQFPN 3x3x1.0 16L package information.

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